

**Notice of References Cited**Application/Control No.  
09/904,129Applicant(s)/Patent Under  
Reexamination  
UEDA, TETSUZOExaminer  
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1765

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**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-6,254,675	07-2001	Aldinger et al.	117/89
	B	US-5,891,790	04-1999	Keller et al.	438/508
	C	US-3,829,556	08-1974	Logan et al.	423/409
	D	US-6,017,807	01-2000	Furukawa et al.	438/502
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Puchinger et al. "Gallium Nitride thin layers via a liquid precursor route" (January 2000). Journal of Crystal Growth, Vol 208, Nos 1-4, pp 153-159.
	V	Lange, F. "Chemical Solution Routes to Single crystal Thin Films" (1996), Science, Vol 273 pp 903-909.
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.